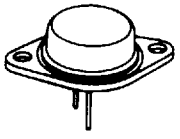
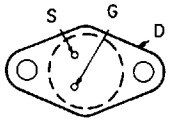
Power MOSFETS

ECG Type	Description and Application	Transconductance gfs µmhos	Drain to Source Breakdown Voltage BV_{DSS}	Gate to Source Breakdown Voltage BV_{GS}	Continuous Drain Current I_D Amps	Gate to Source Threshold Voltage V_{GS} (th)	Drain to Source Resistance r_{DS} (on) Ohms	Input Cap C_{iss} pf	Device Dissipation @T_C=25° C P_D Watts	Package Case/Fig./Basing
ECG2392 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	6 Min	100 Min	±20 Max*	32	4 Max	.06 Max	1500 Max	125 Max	**TO-3** Fig. T28
						td(off) = 300 ns, td(on) = 50 ns, tf = 200 ns, tr = 200 ns				
ECG2386 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	2 Min	600 Min	±20 Max*	6	4.5 Max	1.2 Max	1800 Max	150 Max	
						td(off) = 200 ns, td(on) = 60 ns, tf = 120 ns, tr = 150 ns				
ECG2384 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	1.8 Min	800 Min	±20 Max*	6	4 Max	1.5 Max	3500 Max	125 Max	
						td(off) = 500 ns, td(on) = 60 ns, tf = 100 ns, tr = 100 ns				
ECG2900 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	3 Min	60 Min	±20 Max*	12	4.5 Max	.2 Max	800 Max	75 Max	**TO-220** Fig. T41
						td(off) = 80 ns, td(on) = 60 ns, tf = 110 ns, tr = 160 ns				
ECG2389 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	8 Min	60 Min	±30 Max*	35	4 Max	.045 Max	2000 Max	125 Max	
						td(off) = 160 ns, td(on) = 40 ns, tf = 130 ns, tr = 90 ns				
ECG2395 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	17 Min	60 Min	±30 Max*	50	4 Max	.028 Max	2000 Max	150 Max	
						td(off) = 170 ns, td(on) = 20 ns, tf = 120 ns, tr = 70 ns				
ECG2382 ▲ (Compl to ECG2383)	MOSFET, N-Ch, Enhancement Hi Speed Switch	1.5 Min	100 Min	±20 Max*	8	4 Max	.5 Max	750 Max	75 Max	
						td(off) = 50 ns, td(on) = 50 ns, tf = 60 ns, tr = 120 ns				
ECG2383 ▲ (Compl to ECG2382)	MOSFET, P-Ch, Enhancement Hi Speed Switch	2 Min	100 Min	±20 Max*	8	4.5 Max	.4 Max	1200 Max	75 Max	
						td (off) = 200 ns, td(on) = 80 ns, tf = 150 ns, tr = 150 ns				
ECG66 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	3 Min	100 Min	±20 Max*	12	4.5 Max	.18 Max	1200 Max	75 Max	
						td(off) = 200 ns, td(on) = 50 ns, tf = 100 ns, tr = 100 ns				
ECG2371 ▲	MOSFET, P-Ch, Enhancement Hi Speed Switch	6 Min	100 Min	±20 max*	19	4 Max	.2 Max	1400 Typ	150 Max	
						td(off) = 40 ns, td(on) = 20 ns, tf = 60 ns, tr = 80 ns				
ECG2396 ▲	MOSFET, N-Ch, Enhancement Hi Speed Switch	12 Min	100 Min	±30 Max*	30	4 Max	.057 Max	2000 Max	150 Max	
						td(off) = 150 ns, td(on) = 20 ns, tf = 65 ns, tr = 40 ns				
ECG2372 ▲	MOSFET, P-Ch, Enhancement Hi Speed Switch	1 Min	200 Min	±20 Max*	3.5	4 Max	1.5 Max	350 Typ	40 Max	
						td(off) = 20 ns, td(on) = 20 ns, tf = 20 ns, tr = 30 ns				
ECG2373 ▲	MOSFET P-Ch Enhancement Hi Speed Switch	4 Min	200 Min	±20 max*	11	4 Max	.5 Max	1200 Typ	125 Max	
						td(off) = 50 ns, td(on) = 20 ns, tf = 50 ns, tr = 50 ns				





ECG2392 use Fig. T28A

* Warning - Exceeding BVGS maximum will result in permanent damage to the gate region oxide layer.
▲ Refer to MOSFET Handling Precautions - Page 1-34

Package Outlines - See Page 1-91